



#### SI5406DC-T1-GE3 Information



For Reference Only

Part Number SI5406DC-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 12V 6.9A 1206-8

Package 8-SMD, Flat Lead

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# SI5406DC-T1-GE3 Specifications

Manufacturer Part Number  Manufacturer  Vishay Siliconix  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  8-SMD, Flat Lead  Series  TrenchFET?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  12V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  1.3W (Ta)		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package  8-SMD, Flat Lead  Series  TrenchFET?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  12V  Current - Continuous Drain (Id) @ 25°C  6.9A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  2.5V, 4.5V  Vgs(th) (Max) @ Id  600mV @ 1.2mA (Min)  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +8V  FET Feature  - Power Dissipation (Max)  1.3W (Ta)	Manufacturer Part Number	SI5406DC-T1-GE3
Transistors - FETs, MOSFETs - Single  8-SMD, Flat Lead  Series TrenchFET?  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 12V  Current - Continuous Drain (Id) @ 25°C 6.9A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V  Vgs(th) (Max) @ Id 600mV @ 1.2mA (Min)  Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature - Power Dissipation (Max)  1.3W (Ta)	Manufacturer	Vishay Siliconix
Package 8-SMD, Flat Lead  Series TrenchFET?  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 12V  Current - Continuous Drain (Id) @ 25°C 6.9A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V  Vgs(th) (Max) @ Id 600mV @ 1.2mA (Min)  Gate Charge (Qg) (Max) @ Vgs 20nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max) ±8V  FET Feature -  Power Dissipation (Max) 1.3W (Ta)	Category	Discrete Semiconductor Products
Series Trype N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 6.9A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 600mV @ 1.2mA (Min) Gate Charge (Qg) (Max) @ Vgs 20nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 1.3W (Ta)		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 6.9A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 600mV @ 1.2mA (Min) Gate Charge (Qg) (Max) @ Vgs 20nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) 1.3W (Ta)	Package	8-SMD, Flat Lead
Technology  Drain to Source Voltage (Vdss)  12V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  MOSFET (Metal Oxide)  6.9A (Ta)  6.9A (Ta)  6.9A (Ta)  6.9A (Ta)  6.9A (Ta)  7.5V  7.5V	Series	TrenchFET?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  6.9A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  2.5V, 4.5V  Vgs(th) (Max) @ Id  600mV @ 1.2mA (Min)  Gate Charge (Qg) (Max) @ Vgs  20nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +8V  FET Feature  Power Dissipation (Max)  1.3W (Ta)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 6.9A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V  Vgs(th) (Max) @ Id 600mV @ 1.2mA (Min)  Gate Charge (Qg) (Max) @ Vgs 20nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds -  Vgs (Max) ±8V  FET Feature -  Power Dissipation (Max) 1.3W (Ta)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)         2.5V, 4.5V           Vgs(th) (Max) @ Id         600mV @ 1.2mA (Min)           Gate Charge (Qg) (Max) @ Vgs         20nC @ 4.5V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±8V           FET Feature         -           Power Dissipation (Max)         1.3W (Ta)	Drain to Source Voltage (Vdss)	12V
Vgs(th) (Max) @ Id         600mV @ 1.2mA (Min)           Gate Charge (Qg) (Max) @ Vgs         20nC @ 4.5V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±8V           FET Feature         -           Power Dissipation (Max)         1.3W (Ta)	Current - Continuous Drain (Id) @ 25°C	6.9A (Ta)
Gate Charge (Qg) (Max) @ Vgs       20nC @ 4.5V         Input Capacitance (Ciss) (Max) @ Vds       -         Vgs (Max)       ±8V         FET Feature       -         Power Dissipation (Max)       1.3W (Ta)	Drive Voltage (Max Rds On, Min Rds On)	2.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±8V           FET Feature         -           Power Dissipation (Max)         1.3W (Ta)	Vgs(th) (Max) @ Id	600mV @ 1.2mA (Min)
Vgs (Max)         ±8V           FET Feature         -           Power Dissipation (Max)         1.3W (Ta)	Gate Charge (Qg) (Max) @ Vgs	20nC @ 4.5V
FET Feature - Power Dissipation (Max) 1.3W (Ta)	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) 1.3W (Ta)	Vgs (Max)	$\pm 8V$
-	FET Feature	-
D1 O (M ) © 11 V	Power Dissipation (Max)	1.3W (Ta)
Rds On (Max) @ Id, Vgs 20 mOnm @ 6.9A, 4.5V	Rds On (Max) @ Id, Vgs	20 mOhm @ 6.9A, 4.5V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package 1206-8 ChipFET?	Supplier Device Package	1206-8 ChipFET?
Package / Case 8-SMD, Flat Lead	Package / Case	8-SMD, Flat Lead
Report errors?		Report errors?

#### SI5406DC-T1-GE3 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# SI5406DC-T1-GE3 Payment Methods



















### SI5406DC-T1-GE3 Shipping Methods













If you have any question about SI5406DC-T1-GE3, please do not hesitate to contact us!

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